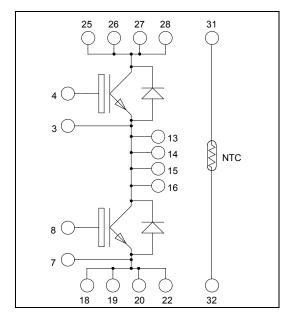
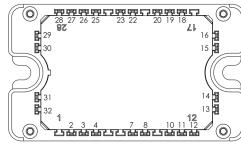


Phase leg High speed IGBT 5 Power Module







Pins 25/26/27/28 ; 13/14/15/16 ; 18/19/20/22 must be shorted together

Application

• Welding converters

- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- High speed IGBT 5
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 100 kHz
 - Low leakage current
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant



Absolute maximum ratings (Per IGBT)

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Voltage		650	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	200	
I _C	Continuous Collector Current $T_{C} = 80^{\circ}C$		120	Α
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	400	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Power Dissipation		483	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



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Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 650V$				200	μA
V _{CE(sat)}	Collector Emitter Saturation Voltage	, GE 10 ,	$T_j = 25^{\circ}C$		1.65	5 2.2	V
			$T_{j} = 150^{\circ}C$		1.9		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2mA$		3.3	4.0	4.7	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				480	nA

Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			12		
Coes	Output Capacitance				0.2		nF
Cres	Reverse Transfer Capacitance	f = 1 MHz		0.044			
Q _G	Gate charge	$V_{GE} = 15V, I_C = 200A$ $V_{CE} = 520V$			480		nC
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)			21		
T _r	Rise Time	$V_{GE} = 15V$			15		ns
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 400V$ $I_{C} = 100A$			180		
$T_{\rm f}$	Fall Time	$R_G = 1\Omega$			18		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = 15V$ $V_{Bus} = 400V$ $I_C = 100A$			20		
Tr	Rise Time				15		
T _{d(off)}	Turn-off Delay Time				205		ns
$T_{\rm f}$	Fall Time	$R_G = 1\Omega$			26		
Eon	Turn on Energy	$V_{GE} = 15V$ $V_{Bus} = 400V$ $I_{C} = 100A$ $R_{G} = 1\Omega$	$T_j = 150^{\circ}C$		3		mI
E _{off}	Turn off Energy		$T_j = 150^{\circ}C$		1.2		mJ
R _{Gint}	Integrated gate resistor				1.25		Ω
R _{thJC}	Junction to Case Thermal Resistance					0.31	°C/W

Diode ratings and characteristics (per diode)

Symbol	Characteristic	teristic Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Peak Repetitive Reverse Voltage					650	V
I _{RM}	Reverse Leakage Current	$V_R = 650V$				200	μA
I _F	DC Forward Current		$Tc = 25^{\circ}C$		200		А
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 200 {\rm A}$ $V_{\rm GE} = 0 {\rm V}$	$T_i = 25^{\circ}C$		1.6	2.2	V
			$T_i = 150^{\circ}C$		1.65		v
t _{rr}	Reverse Recovery Time	I = 100 A	$T_j = 25^{\circ}C$		46		ns
ι _{rr}			$T_{j} = 150^{\circ}C$		62		115
0	Deserve Deservery Change	$v_{\rm R} = 400 v$ di/dt =6000A/µs	$T_j = 25^{\circ}C$		2		
Q _{rr}	Reverse Recovery Charge		$T_{j} = 150^{\circ}C$		4		μC
R _{thJC}	Junction to Case Thermal Resistance					0.35	°C/W



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Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

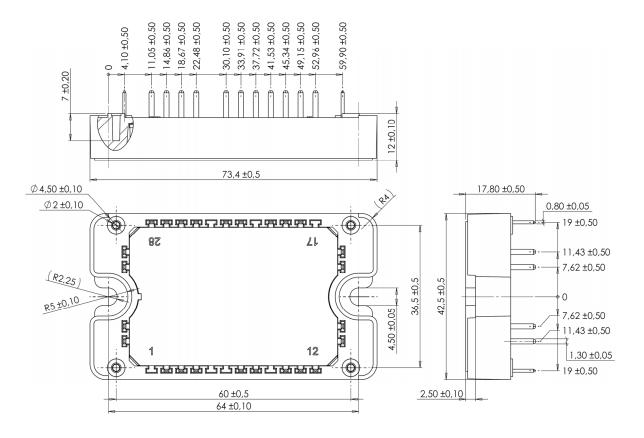
Symbol	Characteristic	,	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		T _C =100°C		4		%
	מ					

 $R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$ T: Thermistor temperature R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T _J	Operating junction temperature range			-40	175	
T _{JOP}	Recommended junction temperature under switching conditions			-40	T _J max -25	°C
T _{STG}	Storage Temperature Range			-40	125	C
T _C	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

Package outline (dimensions in mm)



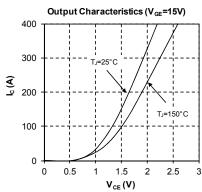
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

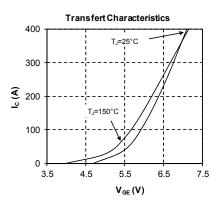
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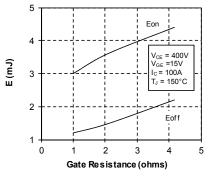
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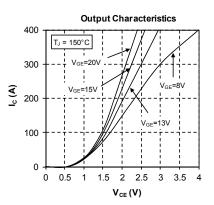
Typical performance curve



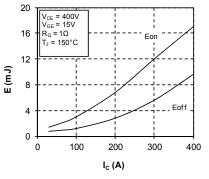


Switching EnergyLosses vs Gate Resistance

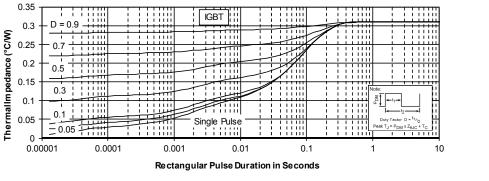




Energy losses vs Collector Current



Maxim um Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration

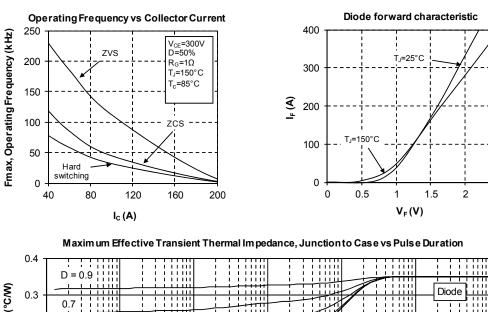


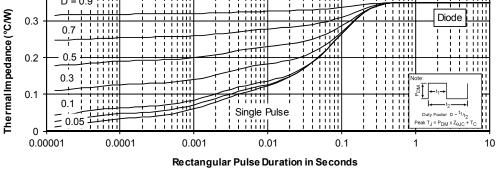
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